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BD355B=BDAP55B;CEMI;CE24;tranz.; PNP;3A;60V;12.5W;10MHz



Dane techniczne:

Nazwa: BD355B

Typ tranzystora: bipolarny

Kierunek przewodnictwa: PNP

Prąd kolektora: 3A

Napięcie kolektor-emiter: 60V

Moc: 12.5W

Częstotliwość: 10MHz

Obudowa: CE24

Producent: CEMI

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isc Silicon PNP Power Transistor

BD355

DESCRIPTION

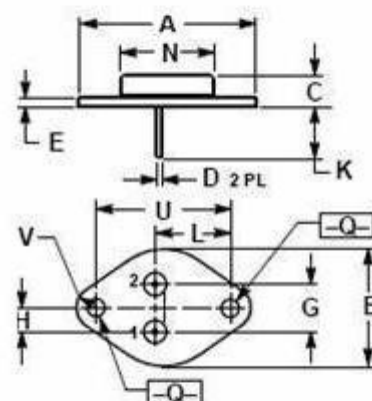
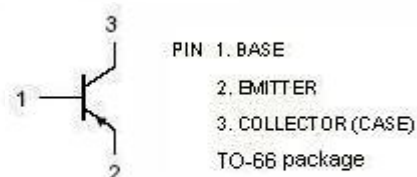
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -60V(\text{Min})$
- Low Saturation Voltage-
: $V_{CE(sat)} = -1.0V(\text{Max}) @ I_C = -2.0A$
- Excellent Safe Operating Area
- Complement to Type BD354
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for general purpose switching and amplifier applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-2	A
I_{CM}	Collector Current-Peak	-4	A
I_B	Base Current-Continuous	-1	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	25	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-65~150	$^\circ\text{C}$



DIM	mm	
	MIN	MAX
A	31.40	31.80
B	17.30	17.70
C	6.70	7.10
D	0.70	0.90
E	1.40	1.60
G	5.08	
H	2.54	
K	9.80	10.20
L	14.70	14.90
N	12.40	12.60
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

isc Silicon PNP Power Transistor**BD355****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -30mA; I _B = 0	-60		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -1mA ; I _E = 0	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -1mA ; I _C = 0	5		V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = -0.5A; I _B = -50mA		-0.5	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = -2A; I _B = -0.2A		-1.0	V
V _{BE(sat)-1}	Base-Emitter Saturation Voltage	I _C = -0.5A; I _B = -50mA		-1.0	V
V _{BE(sat)-2}	Base-Emitter Saturation Voltage	I _C = -2A; I _B = -0.2A		-1.5	V
I _{CEO}	Collector Cutoff Current	V _{CE} = -60V; I _B = 0		-0.2	mA
I _{CBO}	Collector Cutoff Current	V _{CB} = -60V; I _E = 0		-0.1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5.0V; I _C = 0		-0.1	mA
h _{FE-1}	DC Current Gain	I _C = -0.5A; V _{CE} = -4V	30	150	
h _{FE-1}	DC Current Gain	I _C = -2A; V _{CE} = -4V	5		
f _T	Current Gain-Bandwidth Product	I _C = -0.5A; V _{CE} = -10V; f= 1MHz	30		MHz

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